## AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application:

- 1 1. (Currently Amended) A method of forming a microcrystalline silicon thin film,
- 2 comprising:
- 3 supplying, during a first process, a first gas and a second gas to a chamber in which a
- 4 substrate is located;
- supplying, during a second process, the second gas but not the first gas to the chamber;
- depositing a portion of the microcrystalline silicon thin film during the second process;
- 7 and
- 8 performing the first process and second process a plurality of times to form the
- 9 microcrystalline silicon thin film having a target film thickness on the substrate.
- 1 2. (Original) The method of claim 1, wherein supplying the first gas comprises supplying
- 2 SiH<sub>4</sub>, and supplying the second gas comprises supplying H<sub>2</sub>.
- 1 3. (Original) The method of claim 2, wherein performing the first process and second
- 2 process a plurality of times is performed without removing the substrate from the chamber.
- 1 4. (Original) The method of claim 3, further comprising applying an electric field in the
- 2 chamber to break down the SiH<sub>4</sub> to SiH<sub>2</sub>.
- 1 5. (Previously Presented) The method of claim 4, wherein supplying the  $H_2$  comprises
- 2 supplying the H<sub>2</sub> at a generally constant rate, and wherein supplying the SiH<sub>4</sub> comprises
- 3 supplying the SiH<sub>4</sub> at a first rate during the first process but not supplying the SiH<sub>4</sub> during the
- 4 second process.
- 1 6. (Original) The method of claim 4, further comprising depositing the SiH<sub>2</sub> to a surface of
- 2 the substrate during the second process.

- 1 7. (Original) The method of claim 1, further comprising:
- 2 converting the first gas to a third gas; and
- 3 depositing the third gas on the substrate during the second process.
- (Original) The method of claim 7, wherein depositing the third gas on the substrate
- during the second process without supplying the first gas reduces formation of a polymer of the
- 3 third gas prior to depositing of the third gas on the substrate.
- 1 9. (Previously Presented) A method of forming a microcrystalline thin film by activating a
- 2 first source gas containing an element that forms a polymer when a plurality of molecules of the
- 3 element are bonded in a vapor phase, and forming a film having a microcrystalline structure
- 4 primarily composed of said element on a film forming target object, wherein activating the first
- 5 source gas comprises applying an electric field to break down the first source gas to a second
- 6 gas, the method further comprising:
- 7 performing a source supplying process in which said first source gas is supplied, and
- 8 performing a source depositing process in which the supply of said first source gas is
- 9 stopped and said second gas is deposited on the film forming target object to form the
- 10 microcrystalline structure.
- 1 10. (Previously Presented) The method of claim 9, wherein bonding of the second gas is
- 2 suppressed in the source depositing process.
- 1 11. (Previously Presented) The method of claim 9, wherein a third gas that does not form a
- 2 polymer when bonding with itself in the vapor phase is supplied in said source supplying process
- 3 and said source depositing process.
- 1 12. (Previously Presented) The method of claim 11, wherein the third gas is supplied at a
- 2 constant flow rate throughout said source supplying process and said source depositing process.

- 1 13. (Previously Presented) The method of claim 11, wherein a flow rate ratio, r, of said first
- 2 source gas and said third gas satisfies
- 3  $r \ge -(7/12)xP+72.5$ , where P is an electric field intensity density irradiated on said first source
- 4 gas and said third gas.
- 1 14. (Previously Presented) The method of claim 9, wherein performing said source
- 2 supplying process comprises performing the source supplying process for 2 seconds or less, and
- 3 performing said source depositing process comprises performing said source depositing process
- 4 for longer than said source supplying process.
- 1 15. (Previously Presented) The method of claim 11, wherein said first source gas contains
- 2 SiH<sub>4</sub> and said third gas contains  $H_2$ .
- 1 16. (Previously Presented) The method of claim 15, wherein SiH<sub>4</sub> contained in said first
- 2 source gas is broken down to SiH2 in response to the electric field, the second gas comprising
- 3 SiH<sub>2</sub>.
- 1 17. (Original) A method of manufacturing a thin film transistor comprising:
- 2 forming a gate electrode on the substrate;
- 3 forming an insulation layer film on said substrate and said gate electrode,
- 4 forming at least a portion of a channel layer film on said insulation layer by using the
- 5 microcrystalline thin film forming method of claim 9; and
- forming a source/drain electrode on said channel layer.
- 1 18. (Previously Presented) The method of manufacturing a thin film transistor of claim 17,
- 2 wherein forming the channel layer film comprises forming the microcrystalline thin film up to 1
- 3 nm away into the channel layer film from the interface with said insulation layer.
- 1 19.-25. (Cancelled)

- 1 26. (Previously Presented) The method of claim 1, wherein supplying the first gas and
- 2 second gas during the first process comprises supplying the first gas at a first rate and the second
- 3 gas at the second rate, the first rate and second rate defining a flow rate ratio that prevents a thin
- 4 film formed on the substrate from becoming amorphous.
- 1 27. (Previously Presented) The method of claim 26, further comprising applying an electric
- 2 field during the first process, the electric field set at an intensity that in combination with the
- 3 flow rate ratio prevents a thin film formed on the substrate from becoming amorphous.
- 1 28. (Previously Presented) The method of claim 9, further comprising supplying a third gas
- 2 during the source supplying process and during the source depositing process, the first source gas
- 3 and the third gas being supplied at flow rates during the source supplying process to prevent a
- 4 film formed on the film forming target object from becoming amorphous.
- 1 29. (Currently Amended) A method of forming a microcrystalline silicon thin film,
- 2 comprising:
- 3 supplying a first gas and second gas to a chamber in which a substrate is located; and
- 4 depositing the microcrystalline silicon thin film on the substrate, wherein prior to
- 5 depositing the microcrystalline thin film, the supplying of the first gas to the chamber is stopped.
- 1 30. (Currently Amended) The method of claim 29, wherein depositing the microcrystalline
- 2 silicon thin film forms a majority of the microcrystalline silicon thin film on the substrate.